

國立中正大學 107 學年度碩士班招生考試試題

電磁晶片組

系所別：電機工程學系- 計算機工程組
晶片系統組

科目：電子學

光機電整合工程研究所

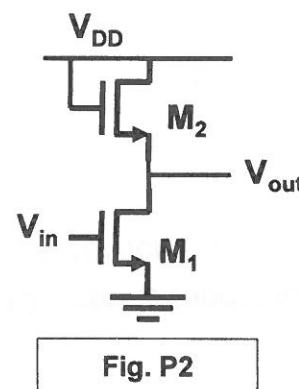
第 2 節

第 1 頁，共 2 頁

1. In each of the following statements, determine whether the statement is **True** or **False**. Describe your reasons to support your choices.
 - (a) By using negative feedback, voltage amplifiers are less sensitive to variations in the amplifier's open-loop gain. (5%)
 - (b) In amplifiers employing negative feedback, frequency compensation is a technique used to extend the closed-loop bandwidth. (5%)
 - (c) For a single-pole operational amplifier, the gain bandwidth product is a constant. (5%)

2. Consider the amplifier shown in Fig. P2,

- (a) Draw the large signal behavior of V_{out} versus V_{in} . (8%)
- (b) Draw the small signal equivalent circuit (8%)
- (c) Derive the voltage gain V_{out}/V_{in} (2%)
- (d) How to maximize the voltage gain? (2%)



3. For the amplifier described by the open-loop transfer function $A(s)$ as below, where $p_1 = 10^5$ Hz, $p_2 = 10^6$ Hz, $p_3 = 10^7$ Hz, this amplifier is used with a frequency-independent feedback network β .

$$A(s) = 10^5 / \left(1 + \frac{s}{p_1}\right) \left(1 + \frac{s}{p_2}\right) \left(1 + \frac{s}{p_3}\right)$$

- (a) Draw the Bode plots (both magnitude and phase plots) of $A(s)$ (8%)
- (b) What is the closed-loop voltage gain that can be obtained for phase margin of 72° ? (7%)

4. Find the close-loop gain of the feedback current amplifier shown in Fig. P4 in case the transconductance is 4 mA/V for Q_1 and Q_2 while ignoring channel length modulation. (15%)

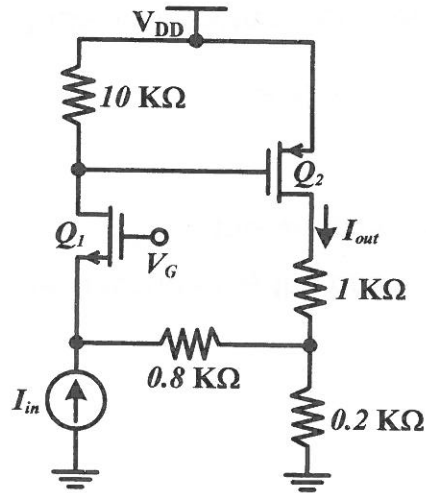


Fig. P4

5. A piece of n-type silicon with uniform doping concentration $N_D = 10^{17}/\text{cm}^3$ is fabricated. If we have a voltage of 1 V across it as shown in Fig. P5, using $n_i = 1.5 \times 10^{10}/\text{cm}^3$, $\mu_p = 480 \text{ cm}^2/\text{V}\cdot\text{s}$, and $\mu_n = 1350 \text{ cm}^2/\text{V}\cdot\text{s}$ to answer the following questions:
- What kind of current is produced? (3%)
 - Compute the total current density. (6%)
 - Compute the resistivity of this n-type silicon. (6%)

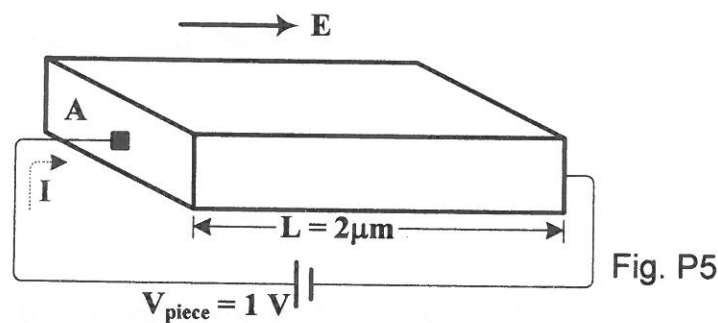


Fig. P5

6. For the circuits shown in Fig. P6, assume $V_{DD} = 1.8 \text{ V}$, $\mu_n C_{ox} = 100 \mu\text{A}/\text{V}^2$, $\mu_p C_{ox} = 50 \mu\text{A}/\text{V}^2$, $V_{tn} = |V_{tp}| = 0.4 \text{ V}$, $\lambda = 0 \text{ V}^{-1}$, $(W/L)_{Q1} = 50$, $(W/L)_{Q2} = 100$, and $R_D = 1 \text{ k}\Omega$.
- Please sketch the voltage transfer characteristic (VTC) for each circuit in Fig. P6. (2%)
 - Assume that input (V_i) has zero rise/fall time and the output time constant is 50 ps for Fig. P6(a), compute the load capacitance and the corresponding low-to-high propagation delay. (6%)
 - Assume $V_i = 0 \text{ V}$ for the circuit shown in Fig. P6(b), compute the output voltage level. (6%)
 - For the situation in (c), compute the static power consumption. (6%)

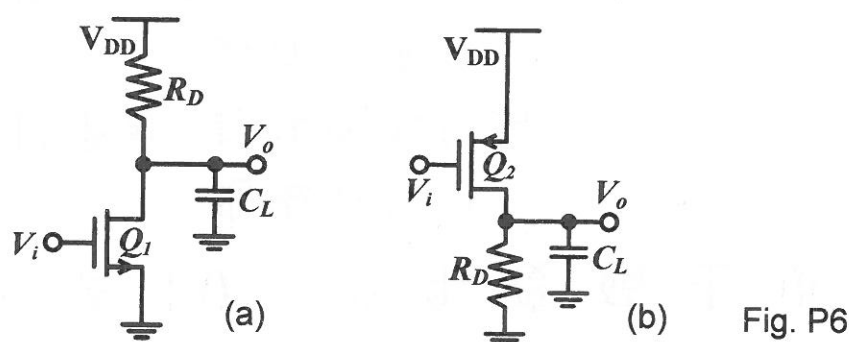


Fig. P6